

**MULTI-LAYERED SUBSTRATE WITH A BUILT-IN CAPACITOR
DESIGN AND A METHOD OF MAKING THE SAME**

BACKGROUND OF THE INVENTION

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1. Field of the Invention

The present invention relates to a multi-layered substrate
manufacture and more particularly to a design of built-in capacitors in
10 flip-chip build-up substrate and in BGA substrate.

2. Description of the Prior Art

Recently, with the advent of the microelectronic devices, the trend
15 of device design is demanded to scale down not only to the
active-devices, such as transistors but also to the passive-devices, such
as resistors in order to increase the integral per unit chip and make the
cost down. The design of the printed circuit board (PCB) used to mount
the IC chip and the interconnection thereof have become a trend of
20 forming the multi-layered PCB as well. In general, a basic PCB is formed
of a dielectric layer and a conductive layer, which has connection thereon.
A multi-layered PCB means several of basic PCB boards assembled
sequentially together. The top layer provides ICs and other electronic
devices (e.g. resistors, capacitors and varieties connectors) supporting
25 and the underlying layers embedded with interconnection circuits. The

interconnection between layer to layer is through the plated through holes or vias.

Referring to Fig.1, for the purpose of alleviating the interference during the signal transferring, the signal plane 10, the power plane 20 and ground plane 30 on the multi-layered substrate are usually designed individually. The signal planes are conductive trace layers mounting on a dielectric layer 15 and 25; for instance, the BT glass fiber, FR4, or the epoxy dielectric layer. However, one of the problems associated with the use of multi-layered substrate is the voltage fluctuation between the power plane 20 and the ground plane 10 or the ground bouncing during the IC circuit operations including switch operations. Particularly, for the devices having high-speed performance, the switch rate becomes sufficiently high. As a result, the voltage fluctuation becomes more and more serious. In order to alleviate the issues and to decrease the noises resulting from the voltage fluctuations, the conventional approach is to use a by-pass capacitor connecting between a power ring 40 and a ground ring 35, which are formed on the top signal layer. The capacitor was connected to the power ring 40 and ground ring 35 through via holes that connect to the power plane 20 and to the ground plane 30, respectively, so as to filter the noises and stabilize the voltages.

The capacitor assembled to the substrate requires extra-steps to pick and place, and thus increases the cycle time of process and decreases the reliability as well. However, the performance of devices on

the high switch frequency operation need a capacitor to maintain it. And for the present IC designs, especially to the PCB used in the computer field, the current in the power plane usually suffers a problem in high frequency (above than 200 MHz). Alternatively, another conventional

5 approach proposed is to use the natural capacitance between power and ground plane. In that method, the thickness of the dielectric layer between the power plane and the ground plane is decreased if it is intended to form sufficient large capacitance. The prior method though solves the cycle time during assembling. However, for the thickness of
10 the dielectric layer 25 between the power plane 20 and the ground plane 30 required special design that the process is flexibless. Besides, another group of the power plane and the ground plane will be required in order to increase the capacitance in advance.

15 In addition to aforementioned PCB, for the purpose of increasing the clock speed of the system and having more multi-functions in unit chip, the devices within a chip are necessary to be drastically increased. As a consequence, the number of a IC chip package leads become very huge. For example, the package of the pin grid array (PGA) has leads
20 over 200 in repose to the demanded of great number of interconnections and the I/O requirement. Furthermore, the flip-chip build up technique and the ball grid array (BGA) etc., have been constructed recently in repose to the high speed devices and a large number of I/O leads. However, with the increasing switching rate in a chip, the noise
25 interference becomes more and more serious than before. Therefore, the

multi-layered substrate for BGA package or flip-chip package chips is necessary having noise decouple capacitors. Unfortunately, in a limited space as a build up substrate or BGA substrate, to build the capacitors are more difficult than general PCB. And thus an object of the present invention herein is to provide a high efficiency method by forming the built-in capacitors, which have more flexibility than prior art.

SUMMARY OF THE INVENTION

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An object of the present invention is to provide a multi-layered substrate with built-in capacitors structure and the manufacture method thereof.

15 An another object of the present invention is to solve the pick and place of exterior capacitor, which is on the top signal layer.

20 The present invention discloses a multi-layered substrate having built-in capacitors. The structure comprises an stack-up substrate of a top signal plane/ a first dielectric layer/ a ground plane/ a second dielectric layer/ a power plane/ a third dielectric layer/ a bottom signal plane. All layers are stacked and sintered as an assembled board. The assembled board has a plurality of via holes therein to connect the wiring on each signal plane, the power plane and the ground plane. In the power plane/ the second dielectric layer/ ground plane stacked layer contains at least one desired build-in capacitor. The build-in capacitor has high permittivity of dielectric material to obtain a sufficient large

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capacitance. The capacitance of the built-in capacitors is easily to adjust by filling different dielectric material into the different via holes and/or combined with adjusting the dielectric layer between power plane and ground plane if it is necessary.

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The method of manufacturing the built-in capacitors in multi-layered substrate proposed by the present invention is to fill a dielectric material into each of predetermined via holes in the dielectric layer between power plane and ground plane. Preferably, the dielectric material used should have a very high dielectric constant value of about two orders of magnitude larger than that of the BT core.

BRIEF DESCRIPTION OF THE DRAWINGS

The foregoing aspects and many of the attendant advantages of this invention will become more readily appreciated as the same becomes better understood by reference to the following detailed description, when taken in conjunction with the accompanying drawings, wherein:

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Fig.1 shows a multi-layered substrate with a by-pass capacitor between power ring and ground ring in accordance with the prior art.

Fig.2 shows a multi-layered substrate with a built-in capacitor between power plane and ground plane in accordance with a preferred embodiment of the present invention.

Fig.3 shows the formation of a plurality of via holes in a multi-layered substrate in accordance with the present invention.

Fig.4 shows a built-in capacitor formed between power plane and ground plane in accordance with a preferred embodiment of the present invention.

Fig.5 shows a multi-layered substrate with a built-in capacitor between power plane and ground plane in accordance with a preferred embodiment of the present invention.

DESCRIPTION OF THE PREFERRED EMBODIMENT

As forgoing prior art depicted, when the multi-layered PCB devices operates at high frequency, it will cause the voltage fluctuations between power plane and ground plane. Especially, the BGA substrate or flip-chip package substrate has more serious problem than the PCB because of the limited space. To solve this issue, the conventional method is to use a by-pass capacitor connecting between power ring and ground ring adjacent to IC chip so as to filter the noises. An alternative method is to design a predetermined dielectric layer thickness associated with areas of the ground plane and power plane to obtain desired capacitance. However, the thickness adjustment so as to obtain the desired capacitance is flexibles. In addition, the assembled process will increase the cycle time.

The motivation of the present invention is thus to propose an efficient method in order to overcome the aforementioned issues,

As is understood by a person skilled in the art, the following
5 four-layer substrate as an embodiment of the present invention are
illustrated of the present invention rather than limiting of the present
invention. It is intended to cover various modifications and similar
arrangements included within the spirit and scope of the appended
claims,

10 Since having a sufficient capacitance of the capacitor in the
multi-layered substrate is demanded to filter the voltage fluctuation
occurred at the power plane or to decrease the ground bouncing. The
structure of the multi-layered substrate with a built-in capacitor is
15 depicted in the Fig.2. In the schematic diagram, the multi-layered
substrate from the bottom sequentially comprises a bottom signal plane
120A, a power plane 130, a ground plane 140 and a top signal plane
150A, and each of the adjacent two layers have a dielectric layer 125,
135, 145 in between.

20 The top signal plane 150A is to support the IC chips (not shown)
and the related electric devices or a single BGA package chip (not shown)
or flip-chip package chips (not shown) and has interconnection wires
thereon to connect the devices. As BGA substrate is concerned, the IC
chip having power pin (not shown) connects to the power ring 160
25 through the wire and the ground pin connects to the ground ring 155. The

ground ring 155 and the power ring 160 through via holes 162,164, respectively, connect to the ground plane 140A and power ring 130A and the others signal planes 150A and 120A.

In addition, the second dielectric layer 135 have extra
5 predetermined via hole for stuffing with a variety of capacitor dielectric material so as to form build-in capacitors with different capacitance. The second dielectric layer 135 is formed of a FR4 glass fiber, BT core etc., which have dielectric constant only about 3.5 to 4.5. To build a desired build-in capacitance by using conventional method, a sufficient thinner
10 dielectric layer is usually required, for example, 0.0015 inch or less. However, using the present method the predetermined via holes stuffs with about two order of magnitude capacitor dielectric material can easily achieve the desired capacitance. And most important, the capacitance is easier to adjust to match the variety requirements only by changing the
15 material. Of course, to change capacitance in the present invention is merely to change the dielectric material. Furthermore, to fill in alternative material and/or combined with reducing the thickness of the dielectric layer can further increase the capacitance.

20 The method of manufacturing built-in capacitors in the multi-layer substrate was depicted as follows.

Referring to Fig. 3, firstly, a plurality of via holes 105 is formed by drilling the stack of the assembled substrate. The via holes 105 are to
25 connect conductive trace layers. The assembled substrate is then

separated. The second dielectric layer 135 is then drilled predetermined a plurality of holes for built-in capacitor formation. The assembled substrate herein comprises a first dielectric layer 145, a second dielectric layer 135, and a third dielectric layer 125. The first dielectric layer has two first conductive layers 140 and 130 thereon, such as copper layer, being respectively mounted on a top and a bottom surface to make as a power plane and a ground plane. The first dielectric layer 145 has a conductive layer 150 thereon prepared for forming the top signal plane. The third dielectric layer 125 has a conductive layer 120 thereon prepared for forming the bottom signal plane too. In a preferred embodiment, the BT core is about 0.25 to 0.6 mm, the via holes 105 are about 200-250 μ m in diameter.

Thereafter, referring to Fig. 4, the predetermined via-holes 108, which are predetermined as capacitors in the second dielectric layer 135 are sealed their respective one open end and filled with high dielectric constant material. In the time, the via holes 105 are sealed. The capacitor dielectric 138 are material, such as the mixture of BaTiO₃ powder and the organic material or the equivalent. After a dry film pattern (not shown) is coated on regions where they are required to electroplate with copper, an etching step is performed to etch away all exposed regions. Subsequently, the dry film is removed and a electroplating step is followed so as to form conductive layer 139 on the conductive trace layer 140A and 130A of the second dielectric layer 135 to form parallel capacitors plates. For BT substrate, the second dielectric layer 135, if the dielectric material 138 has dielectric constant of

about 20~200, the capacitance is about 0.1 μ F to several μ F.

Referring to Fig.5, the first conductive layer 150/ the first dielectric layer 145/ the ground plane 140A/ the second dielectric layer 135/the power plane 130A/ the third dielectric layer 125/ the third conductive layer 120 is then stacked again and sintered to form the primitive multi-layered substrate. Thereafter, patterning the first conductive layer 150 and the third conductive layer 120 is performed as before to form a top signal layer 150A and a bottom signal plane 120A. At the same time, at least one power ring 160 and one ground ring 155 are formed on the top signal plane 150A. Finally, an electroplating process is performed to deposit conductive layer 164 and 162 on the plated through holes so as to connect the power ring 160 and power plane 130A and the ground ring 155 and ground plane 140A.

The present invention has following benefits:

- (1) The method of forming built-in capacitors is easier than that of the conventional method.
- (2) Furthermore, the built-in capacitors are easily to adjust the capacitance. The requirement is only filled different dielectric material into different via holes or combined with adjust the thickness of the second dielectric layer 135 to further alter the capacitance..

As is understood by a person skilled in the art, the foregoing preferred embodiments of the present invention are illustrated of the

present invention rather than limiting of the present invention. It is intended to cover various modifications and similar arrangements included within the spirit and scope of the appended claims, the scope of which should be accorded the broadest interpretation so as to encompass all such modifications and similar structure.

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